

TSMC-01-808B

January 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/696,007 10/29/03

Ming-Fang Wang et al.

A NEW PROCESS FOR INTEGRATION OF A
HIGH DIELECTRIC CONSTANT GATE
INSULATOR LAYER IN A CMOS DEVICE

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

TSMC-01-808B

U.S. Patent 5,972,762 to Wu, "Method of Forming MOSFETs with Recessed Self-Aligned Silicide Gradual S/D Junction," discloses a method for forming recessed S/D silicide S/D junctions.

U.S. Patent 5,970,329 to Cha, "Method of Forming Power Semiconductor Device Having Insulated Gate Electrodes," discloses a recessed source and drain process.

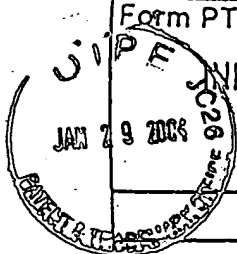
U.S. Patent 5,880,499 to Oyama, "Memory Cell of a Nonvolatile Semiconductor Device," discloses a recessed source and drain.

U.S. Patent 5,491,099 to Hsu, "Method of Making Silicided LDD with Recess in Semiconductor Substrate," discloses a method for a silicided recessed LLD.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large loop at the end.

Stephen B. Ackerman,
Reg. No. 37761



Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		Document Number (Optional) TSMC-01-808B		Application Number 10/696,007	
		Applicant Ming-Fang Wang et al.			
		Filing Date 10/29/03		Group Art Unit	

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5972762	10/26/99	Wu	438	305	1/5/98
	5970329	10/19/99	Cha	438	197	10/14/97
	5880499	3/9/99	Oyama	257	316	8/28/97
	5491099	2/13/96	Hsu	437	35	8/29/94

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.